

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
26 February 2004 (26.02.2004)

PCT

(10) International Publication Number  
**WO 2004/017377 A3**

(51) International Patent Classification<sup>7</sup>: **H01L 21/31**

(21) International Application Number:  
PCT/US2003/025738

(22) International Filing Date: 18 August 2003 (18.08.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:  
60/404,372 18 August 2002 (18.08.2002) US

(71) Applicants (for all designated States except US): **AVIZA TECHNOLOGY, INC.** [US/US]; 440 Kings Village Road, Scotts Valley, CA 95066 (US). **INTEGRATED PROCESS SYSTEMS LTD** [KR/KR]; 33 Jije-dong, Pyunglaek, Kyungki-do (KR).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **LEE, Sang-In**

[KR/US]; 22608 San Juan Road, Cupertino, CA 95014 (US). **SENZAKI, Yoshihide** [JP/US]; 400 Clubhouse Drive, Aptos, CA 95003 (US). **LEE, Sang-Kyoo** [KR/KR]; #201, 17-22 Yangjae 1 Dong, Suhcho-Gu, Seoul (KR).

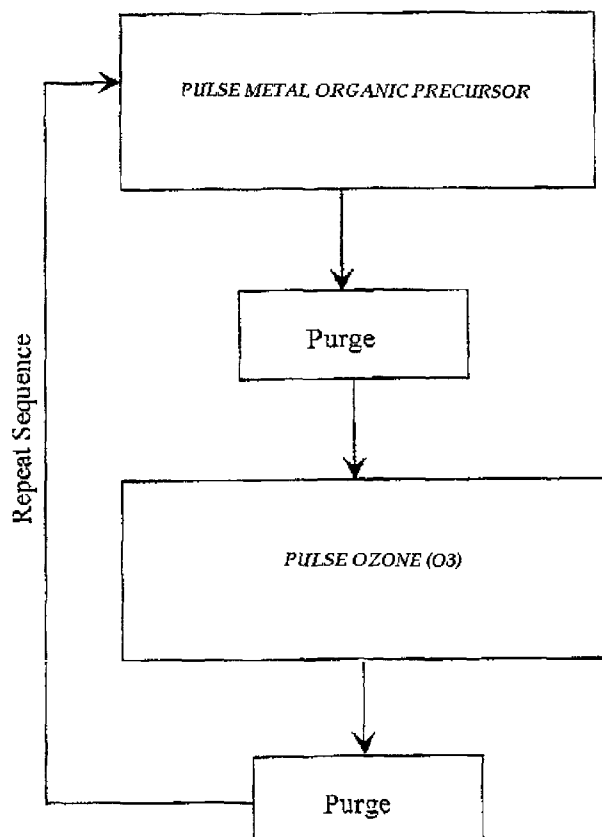
(74) Agents: **SWIATEK, Maria, S.** et al.; Dorsey & Whitney LLP, 4 Embarcadero Center, Suite 3400, San Francisco, CA 94111 (US).

(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW),

[Continued on next page]

(54) Title: ATOMIC LAYER DEPOSITION OF HIGH K METAL OXIDES



(57) Abstract: The present invention relates to the atomic layer deposition ("ALD") of high k dielectric layers of metal oxides containing Group 4 metals, including hafnium oxide, zirconium oxide, and titanium oxide. More particularly, the present invention relates to the ALD formation of Group 4 metal oxide films using an metal alkyl amide as a metal organic precursor and ozone as a co-reactant.

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Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),  
European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE,  
ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO,  
SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM,  
GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

**(88) Date of publication of the international search report:**  
1 July 2004

*For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.*

**Published:**

- *with international search report*
- *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*